

(3) Kindly amend Claim 4 as follows:

4. (Amended) The method of Claim 1 wherein the openings are laterally adjacent portions of the conductive layer with no openings extending through the conductive layer.

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(4) Kindly cancel Claims 6-7 and 10 without prejudice or disclaimer.

(5) Kindly amend Claim 12 as follows:

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12. (Amended) The method of Claim 1 where in the openings extend into the semiconductor substrate.

[ (6) Kindly amend Claim 13 as follows: ]

13. (Amended) The method of Claim 1 wherein the openings substantially terminate at a surface of the semiconductor substrate.

[ (7) Kindly amend Claim 14 as follows: ]

14. (Amended) A method for making a radio frequency (RF) component comprising:  
forming a dielectric layer on a semiconductor substrate;  
forming and patterning a conductive layer on the dielectric layer to define the RF component;  
forming a plurality of openings on opposing sides and through the dielectric layer at least to the semiconductor substrate the openings having a diameter ranging from about 0.5 to about 20 microns and substantially uniform spacing between adjacent openings in a range of about 20 to about 200 microns; and

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releasing the RF component from the semiconductor substrate by exposing the semiconductor substrate to a dry etchant comprising  $\text{XeF}_2$  passing through the openings to the semiconductor substrate.

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(8) Kindly cancel Claims 15-16, 18-19 without prejudice or disclaimer.

(9) Kindly amend Claim 23 as follows:

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23. (Amended) A method for making a radio frequency (RF) component comprising:  
forming a dielectric layer on a semiconductor substrate;  
forming and patterning a conductive layer on the dielectric layer to define the RF component;  
forming a plurality of openings on opposing sides and through the dielectric layer in a predetermined pattern at least to the semiconductor substrate the openings having a diameter ranging from about 0.5 to about 20 microns and substantially uniform spacing between adjacent openings in a range of about 20 to about 200 microns; and

releasing the RF component from the semiconductor substrate by exposing the semiconductor passing through substrate to a dry etchant comprising  $\text{XeF}_2$  passing the openings to the semiconductor substrate.

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(10) Kindly cancel Claim 25 without prejudice or disclaimer.